Low Skew, 1-to-4, LVCMOS/LVTTL-to-LVDS Fanout Buffer

854105

DATA SHEET

General Description

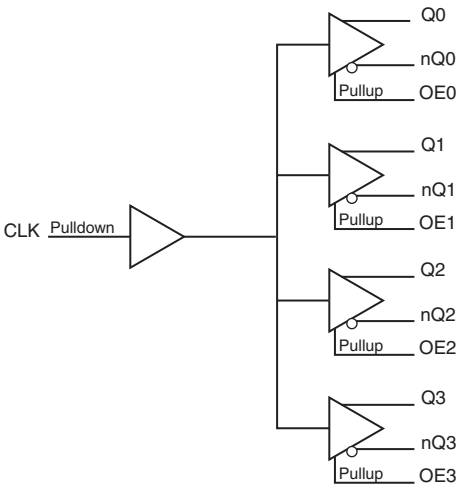
The 854105 is a low skew, high performance 1-to-4 LVCMOS/LVTTL-to-LVDS Clock Fanout Buffer. Utilizing Low Voltage Differential Signaling (LVDS), the 854105 provides a low power, low noise solution for distributing clock signals over controlled impedances of 100Ω. The 854105 accepts an LVCMOS/LVTTL input level and translates it to LVDS output levels.

Guaranteed output and part-to-part skew characteristics make the 854105 ideal for those applications demanding well defined performance and repeatability.

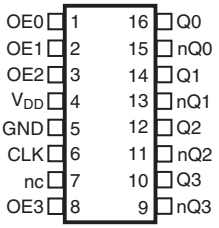
Features

- Four differential LVDS output pairs
- One single-ended LVCMOS/LVTTL input
- CLK can accept the following input levels: LVCMOS, LVTTL
- Maximum output frequency: 250MHz
- Translates single-ended input signals to LVDS levels
- Additive phase jitter, RMS: 0.16ps (typical)
- Output skew: 55ps (maximum)
- Part-to-part skew: 350ps (maximum)
- Propagation delay: 1.62ns (maximum)
- 3.3V operating supply
- 0°C to 70°C ambient operating temperature
- Available in lead-free (RoHS 6) package

Block Diagram



Pin Assignment



854105

16-Lead TSSOP
4.4mm x 5.0mm x 0.925mm package body
G Package
Top View

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Table 1. Pin Descriptions

Number	Name	Type		Description
1	OE0	Input	Pullup	Output enable pin for Q0, nQ0 outputs. See Table 3. LVCMOS/LVTTL interface levels.
2	OE1	Input	Pullup	Output enable pin for Q1, nQ1 outputs. See Table 3. LVCMOS/LVTTL interface levels.
3	OE2	Input	Pullup	Output enable pin for Q2, nQ2 outputs. See Table 3. LVCMOS/LVTTL interface levels.
4	V_{DD}	Power		Positive supply pin.
5	GND	Power		Power supply ground.
6	CLK	Input	Pulldown	Single-ended clock input. LVCMOS/LVTTL interface levels.
7	nc	Unused		No connect.
8	OE3	Input	Pullup	Output enable pin for Q3, nQ3 outputs. See Table 3. LVCMOS/LVTTL interface levels.
9, 10	nQ3, Q3	Output		Differential output pair. LVDS interface levels.
11, 12	nQ2, Q2	Output		Differential output pair. LVDS interface levels.
13, 14	nQ1, Q1	Output		Differential output pair. LVDS interface levels.
15, 16	nQ0, Q0	Output		Differential output pair. LVDS interface levels.

NOTE: *Pullup and Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics,* for typical values.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C_{IN}	Input Capacitance			4		pF
R_{PULLUP}	Input Pullup Resistor			51		kΩ
$R_{PULLDOWN}$	Input Pulldown Resistor			51		kΩ

Function Table

Table 3. Output Enable Function Table

Inputs	Outputs
OE[3:0]	**Q[3:0], nQ[3:0]**
0	High-Impedance
1	Active (default)

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Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics or AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V_{DD}	4.6V
Inputs, V_I	-0.5V to V_{DD} + 0.5V
Outputs, I_O (LVDS) Continuos Current Surge Current	 10mA 15mA
Package Thermal Impedance, θ_{JA}	100.3°C/W (0 mps)
Storage Temperature, T_{STG}	-65°C to 150°C

DC Electrical Characteristics

Table 4A. LVDS Power Supply DC Characteristics, V_{DD} = 3.3V ± 5%, T_A = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Positive Supply Voltage		3.135	3.3	3.465	V
I_{DD}	Power Supply Current				75	mA

Table 4B. LVCMOS/LVTTL DC Characteristics, V_{DD} = 3.3V ± 5%, T_A = 0°C to 70°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage			2		V_{DD} + 0.3	V
V_{IL}	Input Low Voltage			-0.3		0.8	V
I_{IH}	Input High Current	CLK	$V_{DD} = V_{IN}$ = 3.465V			150	µA
		OE[3:0]	$V_{DD} = V_{IN}$ = 3.465V			5	µA
I_{IL}	Input Low Current	CLK	V_{DD} = 3.465V, V_{IN} = 0V	-5			µA
		OE[3:0]	V_{DD} = 3.465V, V_{IN} = 0V	-150			µA

Table 4C. LVDS DC Characteristics, V_{DD} = 3.3V ± 5%, T_A = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{OD}	Differential Output Voltage		250	350	450	mV
ΔV_{OD}	V_{OD} Magnitude Change				50	mV
V_{OS}	Offset Voltage		1.15	1.3	1.45	V
ΔV_{OS}	V_{OS} Magnitude Change				50	mV

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Table 5. AC Characteristics, V_{DD} = 3.3V ± 5%, T_A = 0°C to 70°C

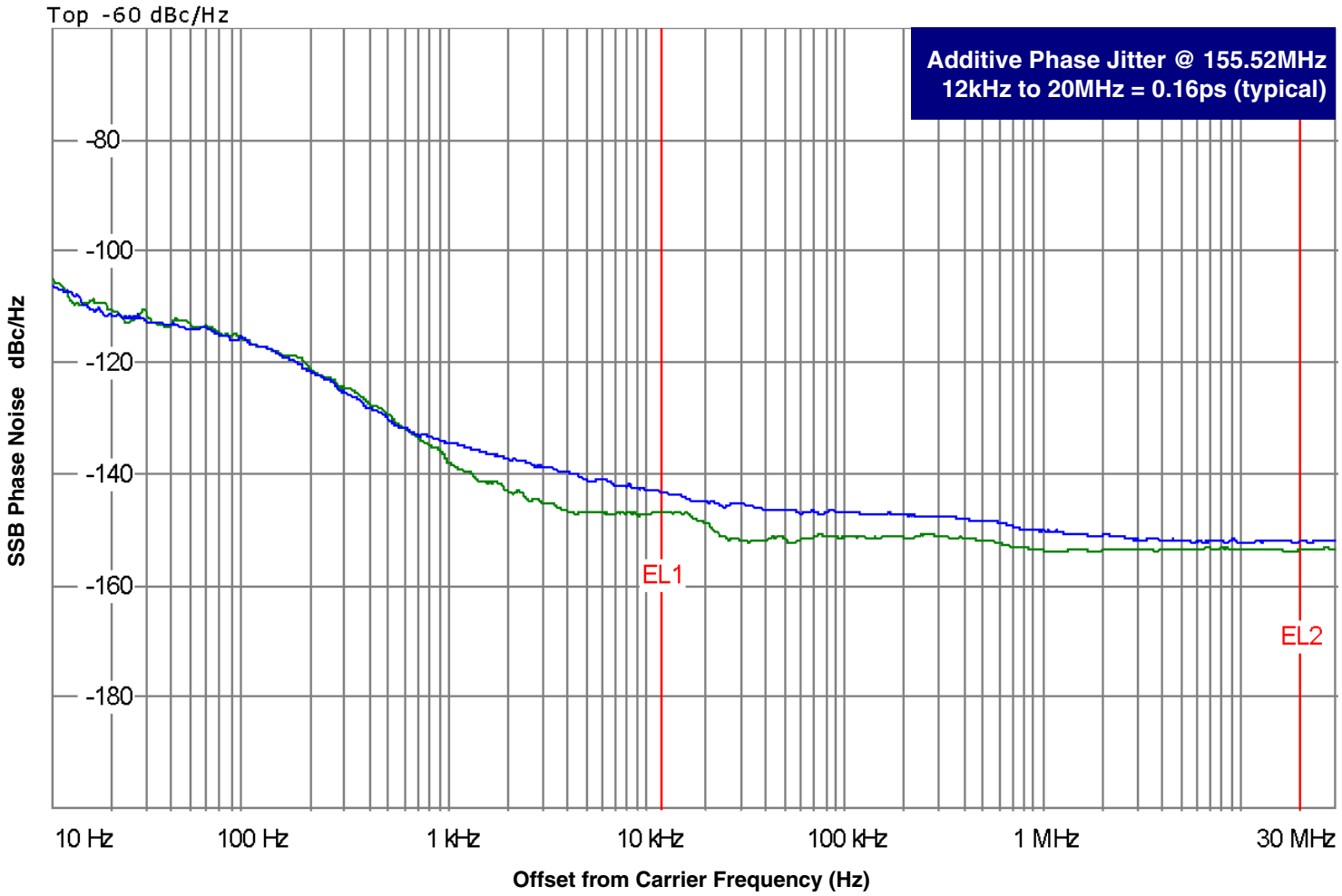
Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{MAX}	Output Frequency				250	MHz
t_{PD}	Propagation Delay; NOTE 1		1.0		1.62	ns
*t*jit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section	155.52MHz, Integration Range: (12kHz – 20MHz)		0.16		ps
tsk(o)	Output Skew; NOTE 2, 4				55	ps
tsk(pp)	Part-to-Part Skew; NOTE 3, 4				350	ps
t_R / t_F	Output Rise/Fall Time	20% to 80%	130		660	ps
odc	Output Duty Cycle	*f* ≤ 133MHz	45		55	%
		f >133MHz	40		60	%

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.
NOTE: All parameters measured at f_{MAX} unless noted otherwise.
NOTE 1: Measured from $V_{DD}/2$ of the input to the differential output crossing point.
NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the output differential crossing point.
NOTE 3: Defined as skew between outputs on different devices operating at the same supply voltage, same temperature and with equal load conditions. Using the same type of input on each device, the outputs are measured at the differential cross points.
NOTE 4: This parameter is defined in accordance with JEDEC Standard 65.

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Additive Phase Jitter

The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the ***dBc Phase Noise.*** This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio of the power in the 1Hz band to the power in the fundamental. When the required offset is specified, the phase noise is called a ***dBc*** value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.

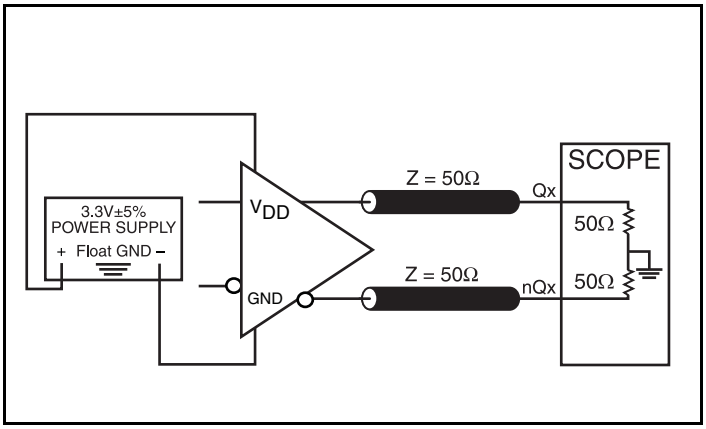


As with most timing specifications, phase noise measurements has issues relating to the limitations of the equipment. Often the noise floor of the equipment is higher than the noise floor of the device. This is illustrated above. The device meets the noise floor of what is shown, but can actually be lower. The phase noise is dependent on the input source and measurement equipment.

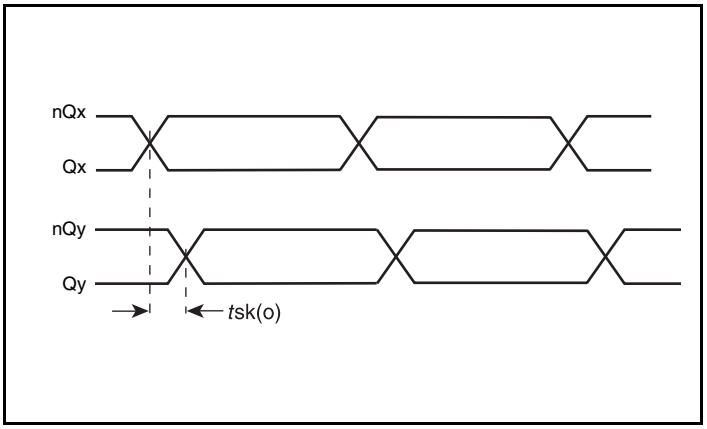
The source generator "Rohde & Schwarz SMA100 Signal Generator as external input to an Agilent 8133A 3GHz Pulse Generator".

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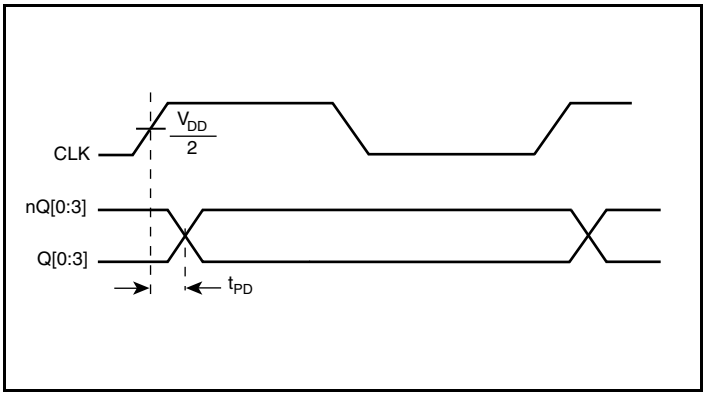
Parameter Measurement Information



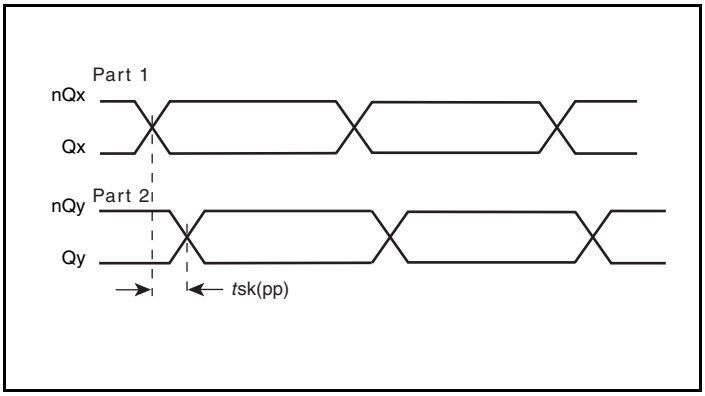
3.3V LVDS Output Load AC Test Circuit



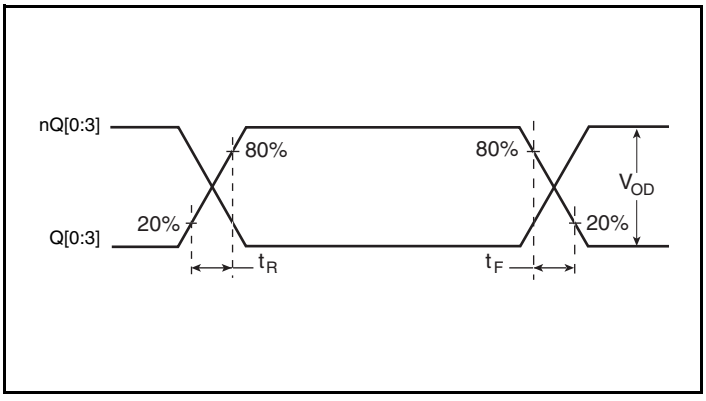
Output Skew



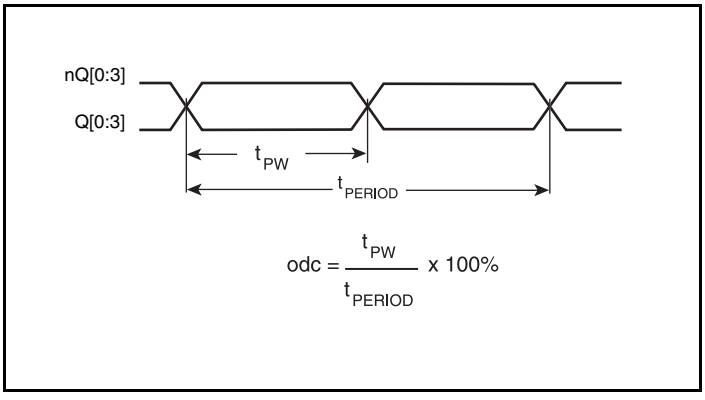
Propagation Delay



Part-to-Part Skew



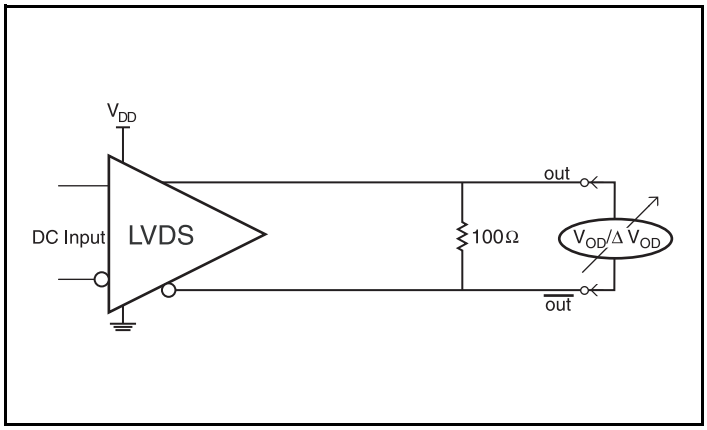
Output Rise/Fall Time



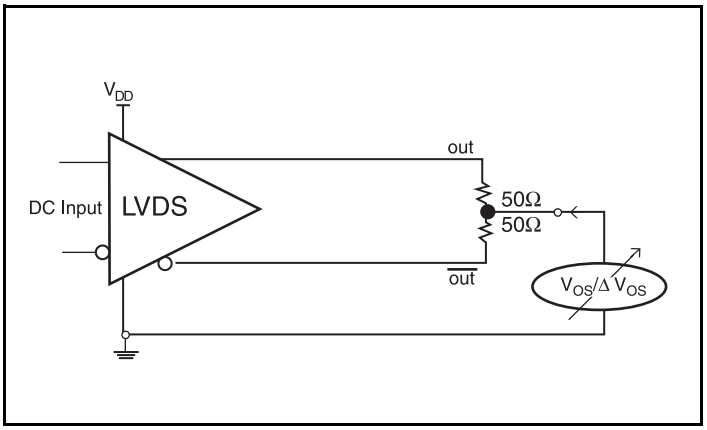
Output Duty Cycle/Pulse Width/Period

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Parameter Measurement Information, continued



Differential Output Voltage Setup



Offset Voltage Setup

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Application Information

Recommendations for Unused Input and Output Pins

Inputs:

LVCMOS Control Pins

All control pins have internal pullups; additional resistance is not required but can be added for additional protection. A 1kΩ resistor can be used.

Outputs:

LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100Ω across. If they are left floating, there should be no trace attached.

3.3V LVDS Driver Termination

A general LVDS interface is shown in *Figure 1.* In a 100Ω differential transmission line environment, LVDS drivers require a matched load termination of 100Ω across near the receiver input. For a multiple LVDS outputs buffer, if only partial outputs are used, it is recommended to terminate the unused outputs.

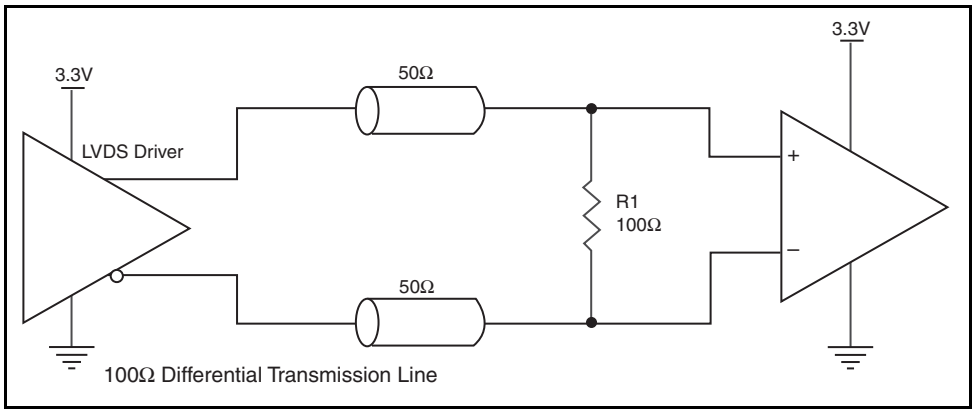


Figure 1. Typical LVDS Driver Termination

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Power Considerations

This section provides information on power dissipation and junction temperature for the 854105.
Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the 854105 is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for V_{DD} = 3.3V + 5% = 3.465V, which gives worst case results.

- Power $(core)_{MAX} = V_{DD_MAX} * I_{DD_MAX}$ = 3.465V * 75mA = **259.875mW**

2. Junction Temperature.

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, Tj, to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for Tj is as follows: $Tj = \theta_{JA} * Pd_total + T_A$

Tj = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 100.3°C/W per Table 6 below.

Therefore, Tj for an ambient temperature of 70°C with all outputs switching is:

70°C + 0.260W * 100.3°C/W = 96.1°C. This is well below the limit of 125°C.

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 6. Thermal Resistance θ_{JA} for 16 Lead TSSOP, Forced Convection

θ_{JA} by Velocity			
Meters per Second	**0**	**1**	**2.5**
Multi-Layer PCB, JEDEC Standard Test Boards	100.3°C/W	96.0°C/W	93.9°C/W

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Reliability Information

Table 7. θ_{JA} vs. Air Flow Table for a 16 Lead TSSOP

θ_{JA} by Velocity			
Meters per Second	**0**	**1**	**2.5**
Multi-Layer PCB, JEDEC Standard Test Boards	100.3°C/W	96.0°C/W	93.9°C/W

Transistor Count

The transistor count for 854105 is: 286

Package Outline and Package Dimensions

Package Outline - G Suffix for 16 Lead TSSOP

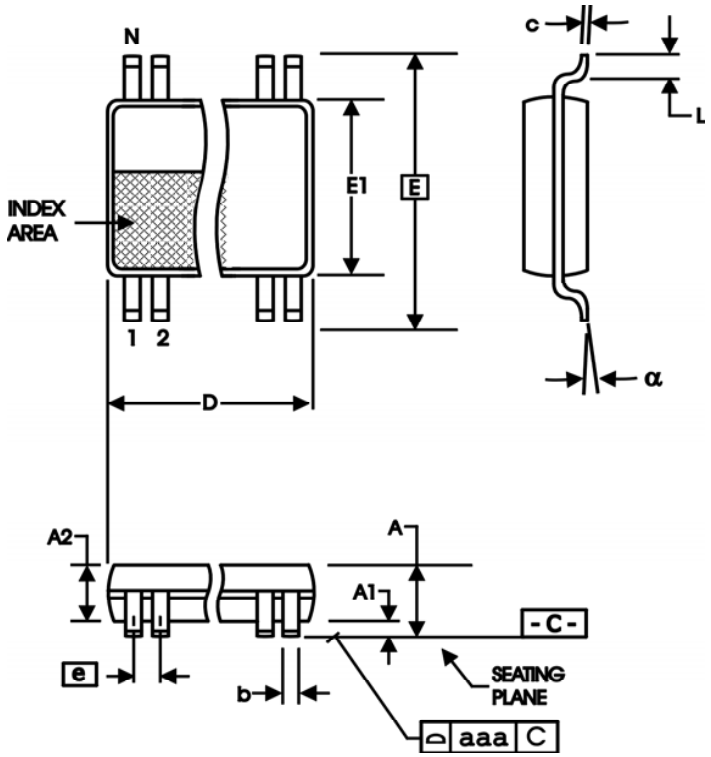


Table 8. Package Dimensions

All Dimensions in Millimeters		
Symbol	**Minimum**	**Maximum**
N	16	
A		1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	4.90	5.10
E	6.40 Basic	
E1	4.30	4.50
e	0.65 Basic	
L	0.45	0.75
α	0°	8°
aaa		0.10

Reference Document: JEDEC Publication 95, MO-153

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Ordering Information

Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
854105AGLF	854105AL	“Lead-Free” 16 Lead TSSOP	Tube	0°C to 70°C
854105AGLFT	854105AL	“Lead-Free” 16 Lead TSSOP	Tape & Reel	0°C to 70°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

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Revision History Sheet

Rev	Table	Page	Description of Change	Date
A	T9	11	Ordering Information - removed leaded devices. Updated data sheet format.	7/10/15

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